

Supporting Information

Aqueous Solution-Phase Selenized CuIn(S,Se)₂ Thin Film Solar Cells Annealed under Inert Atmosphere

Yunjung Oh,[†] Wooseok Yang,[†] Jimin Kim,[†] Kyoohye Woo,[‡] and Jooho Moon^{†,}*

[†]Department of Materials Science and Engineering, Yonsei University

50 Yonsei-ro Seodaemun-gu, Seoul, 120-749, Republic of Korea

[‡]Advanced Manufacturing Systems Research Division, Korea Institute of Machinery and

Materials, 156 Gajeongbuk-ro, Yuseong-gu, Daejeon 305-343, Republic of Korea

*Corresponding author, e-mail: jmoon@yonsei.ac.kr, tel.: +82-2-2123-2855, fax: +82-2-365-5882.

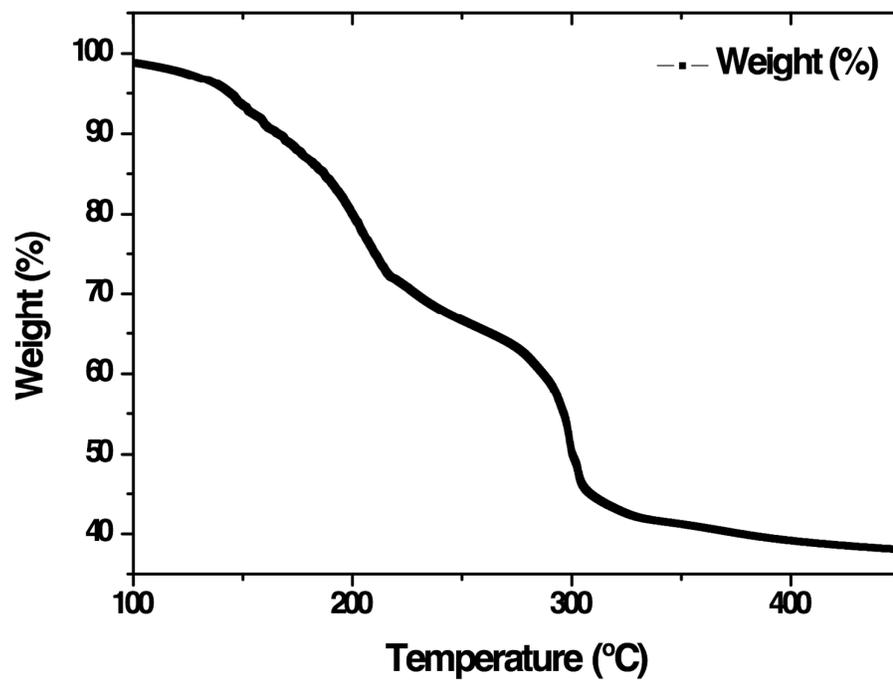


Figure S1. TG analysis of aqueous-based Cu-In-S ink. This analysis was performed in an air atmosphere at 150 cc min^{-1} with a heating rate of $10 \text{ }^\circ\text{C min}^{-1}$.

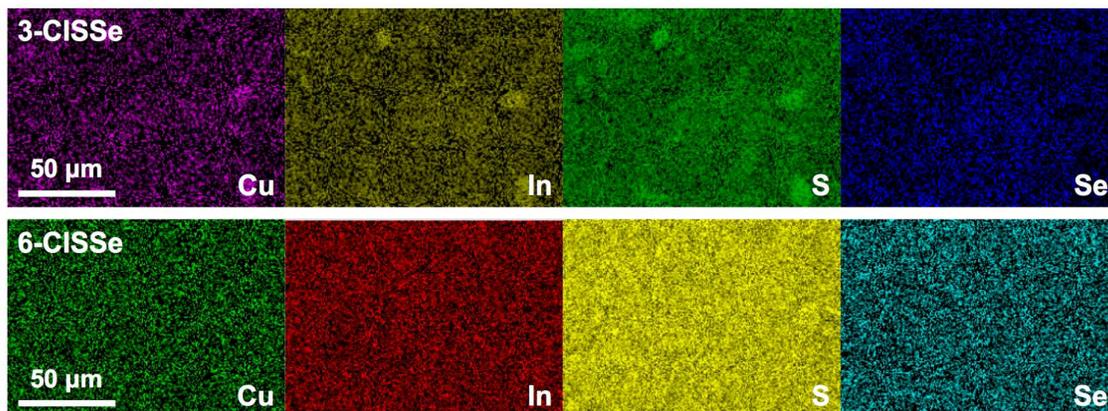


Figure S2. Compositional mapping images of CISSe film surfaces.

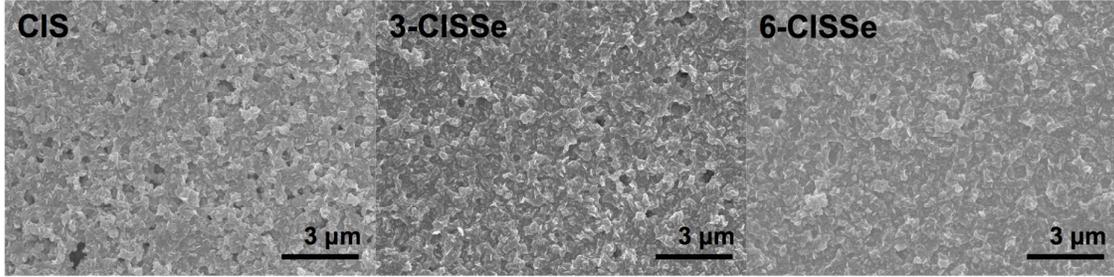


Figure S3. Surface microstructure of the as-prepared CIS/CISSe absorber layer.

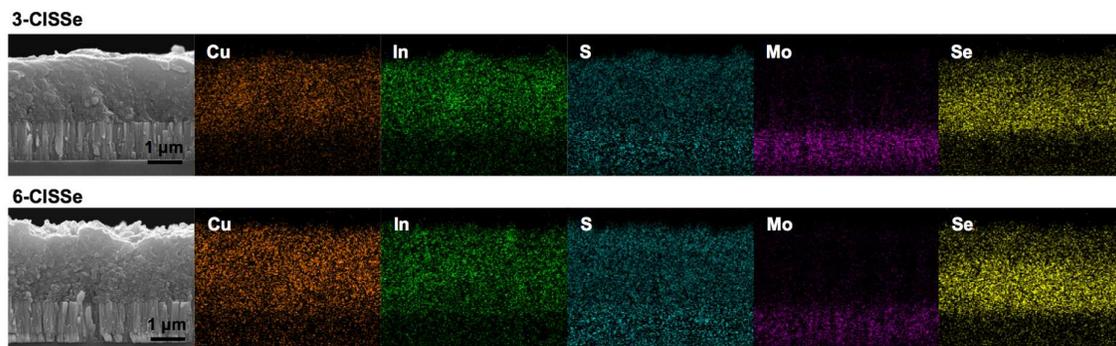


Figure S4. Cross-sectional EDX mapping of ASP-CISSe layers deposited on Mo/SLG substrate.

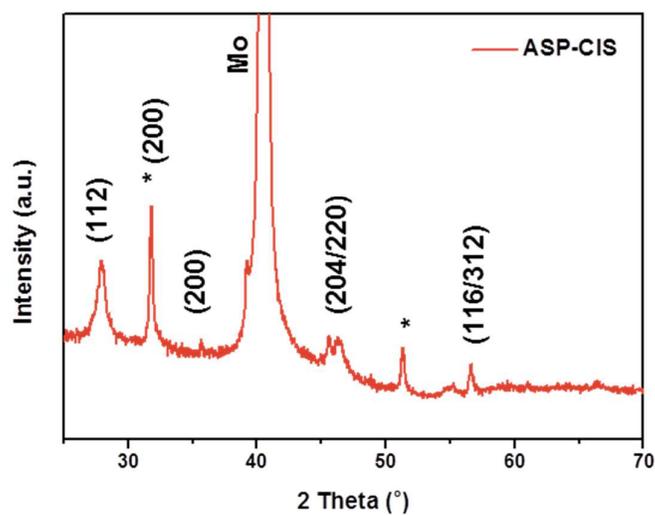


Figure S5. XRD results for ASP-CIS film deposited on Mo-coated substrate. All samples were dried in ambient air at 300 °C. Asterisks in the figure indicate binary metal sulfide secondary phase.

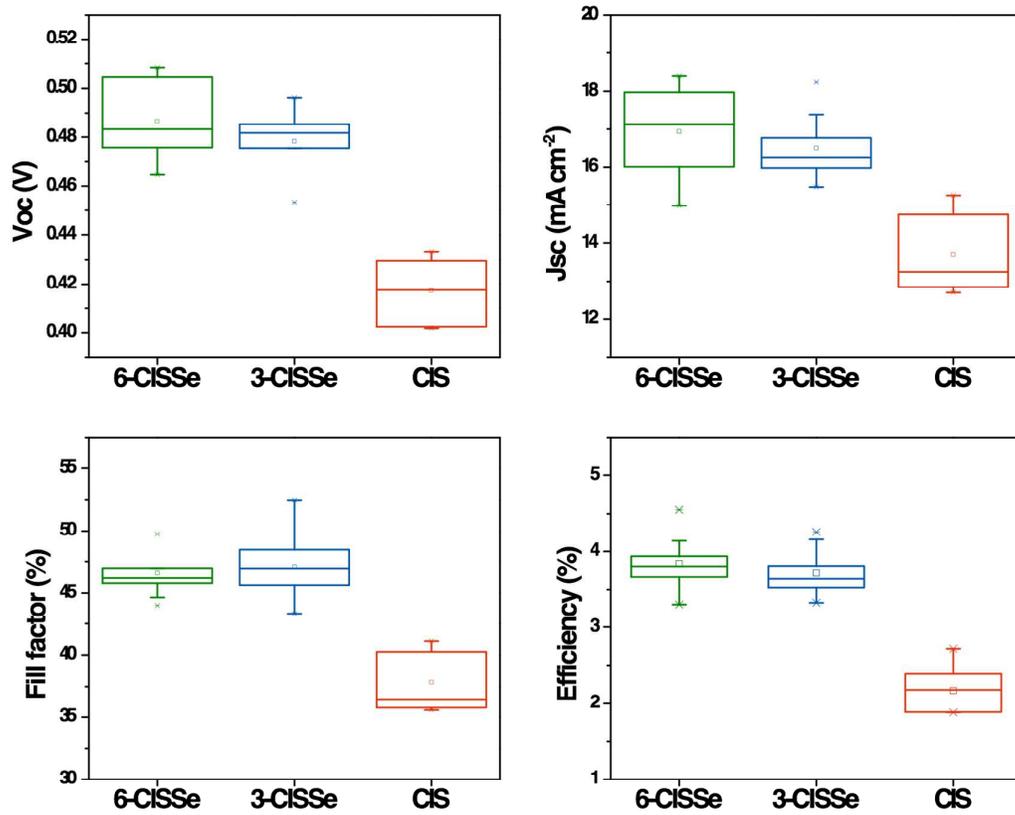


Figure S6. V_{oc} , J_{sc} , FF, and efficiency of CIS/CISse solar cells.

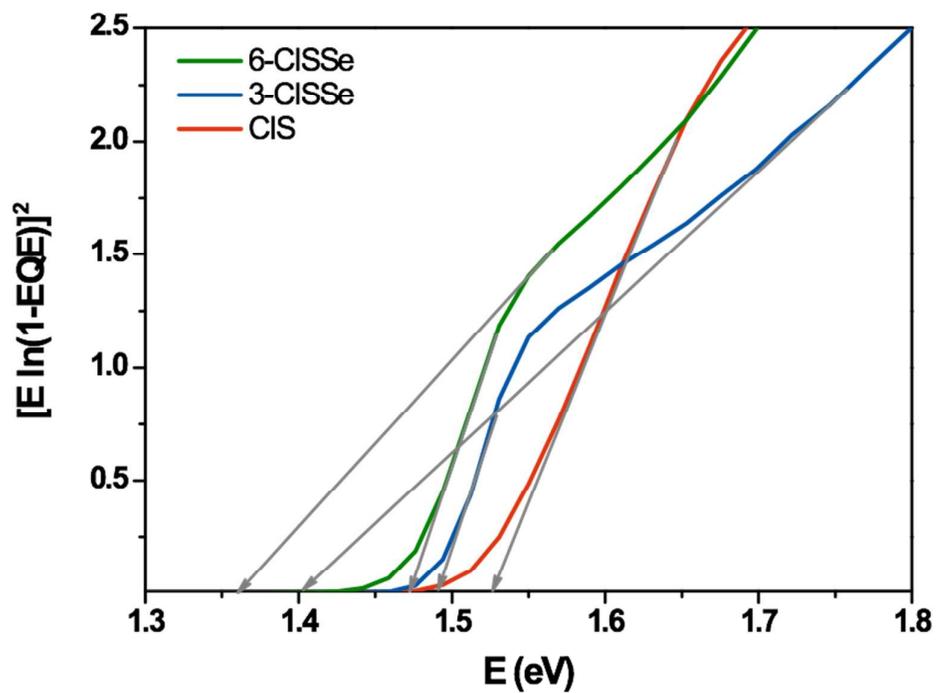


Figure S7. The band gap of CIS was determined to be 1.53 eV by fitting a plot of $[E \ln(1-EQE)]^2$ vs. E near the band edge. 3-CISSe and 6-CISSe had band gaps in the range of 1.40 – 1.49 eV and 1.36 – 1.46 eV, respectively.